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Infineon® LITIXTM Basic

TLD1311EL

3 Channel High Side Current Source

Data Sheet

Rev. 1.1, 2015-03-19

Automotive

TLD1311EL



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3 Channel High Side Current Source LITIX[™] Basic

TLD1311EL





1 Overview

Features

- 3 Channel device with integrated output stages (current sources), optimized to drive LEDs
- Output current up to 120mA per channel
- · Low current consumption in sleep mode
- PWM-operation supported via VS- and EN-pin
- Output current adjustable via external low power resistor and possibility to connect PTC resistor for LED protection during over temperature conditions
- · Reverse polarity protection
- Overload protection
- Undervoltage detection
- Infineon® N-1 detection functionality
- Wide temperature range: -40 °C < T_i < 150 °C
- PG-SSOP14 package with exposed heatslug
- Green Product (RoHS compliant)
- AEC Qualified



PG-SSOP14

Description

The LITIXTM Basic TLD1311EL is a three channel high side driver IC with integrated output stages. It is designed to control LEDs with a current up to 120 mA. In typical automotive applications the device is capable to drive i.e. 3 red LEDs per chain (total 9 LEDs) with a current up to 60mA, which is limited by thermal cooling aspects. The output current is controlled practically independent of load and supply voltage changes.

Table 1 Product Summary

Operating voltage	$V_{S(nom)}$	5.5 V 40 V
Maximum voltage	$V_{ m S(max)} \ V_{ m OUTx(max)}$	40 V
Nominal output (load) current	$I_{OUTx(nom)}$	60 mA when using a supply voltage range of 8V - 18V (e.g. Automotive car battery). Currents up to $I_{\rm OUT(max)}$ possible in applications with low thermal resistance $R_{\rm thJA}$
Maximum output (load) current	$I_{OUTx(max)}$	120 mA; depending on thermal resistance $R_{\rm thJA}$
Output current accuracy at $R_{\rm SET}$ = 12 k Ω	k_{LT}	$750 \pm 7\%$
Current consumption in sleep mode	$I_{S(sleep,typ)}$	0.1 μΑ

Туре	Package	Marking
TLD1311EL	PG-SSOP14	TLD1311EL

Data Sheet 3 Rev. 1.1, 2015-03-19



Overview

Protective functions

- ESD protection
- Under voltage lock out
- Over Load protection
- Over Temperature protection
- Reverse Polarity protection

Diagnostic functions

- N-1 detection, latched function
- SC to Vs (indicated by N-1 diagnosis)

Applications

Designed for exterior LED lighting applications such as tail/brake light, turn indicator, position light, side marker,... The device is also well suited for interior LED lighting applications such as ambient lighting, interior illumination and dash board lighting.



Block Diagram

2 Block Diagram

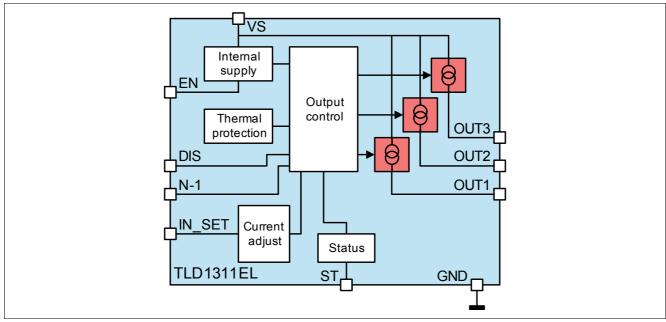


Figure 1 Basic Block Diagram



Pin Configuration

3 Pin Configuration

3.1 Pin Assignment

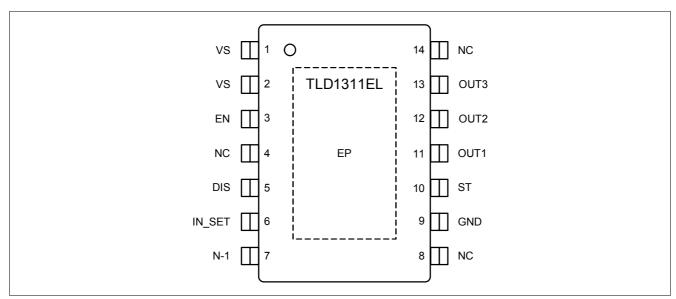


Figure 2 Pin Configuration



Pin Configuration

3.2 Pin Definitions and Functions

Pin	Symbol	Input/ Output	Function
1, 2	VS	-	Supply Voltage; battery supply, connect a decoupling capacitor (100 nF - 1 μ F) to GND
3	EN	I	Enable pin
4	NC	_	Pin not connected
5	DIS	I	Disable Input
6	IN_SET	I/O	Input / SET pin; Connect a low power resistor to adjust the output current
7	N-1	I/O	N-1 pin
8	NC	_	Pin not connected
9	GND	_	1) Ground
10	ST	I/O	Status pin
11	OUT1	0	Output 1
12	OUT2	0	Output 2
13	OUT3	0	Output 3
14	NC	_	Pin not connected
Exposed Pad	GND	_	1) Exposed Pad; connect to GND in application

¹⁾ Connect all GND-pins together.



General Product Characteristics

4 General Product Characteristics

4.1 Absolute Maximum Ratings

Absolute Maximum Ratings 1)

 T_j = -40 °C to +150 °C; all voltages with respect to ground, positive current flowing into pin for input pins (I), positive currents flowing out of the I/O and output pins (O) (unless otherwise specified)

Pos.	Parameter	Symbol	Limit	Values	Unit	Conditions
			Min.	Max.		
Voltage	s	-				
4.1.1	Supply voltage	V_{S}	-16	40	V	_
4.1.2	Input voltage EN	V_{EN}	-16	40	V	_
4.1.3	Input voltage EN related to $V_{\rm S}$	$V_{EN(VS)}$	V _S - 40	V _S + 16	V	_
4.1.4	Input voltage EN related to $V_{\rm OUTx}$ $V_{\rm EN}$ - $V_{\rm OUTx}$	V_{EN} - V_{OUTx}	-16	40	V	_
4.1.5	Output voltage	V_{OUTx}	-1	40	V	_
4.1.6	Power stage voltage $V_{PS} = V_{S} - V_{OUTx}$	V_{PS}	-16	40	V	_
4.1.7	Input voltage DIS	V_{DIS}	-0.3	6	V	_
4.1.8	IN_SET voltage	V_{IN_SET}	-0.3	6	V	_
4.1.9	N-1 voltage	V _{N-1}	-0.3	6	V	_
4.1.10	Status voltage	V_{ST}	-0.3	6	V	_
Current	s					
4.1.11	IN_SET current	I_{IN_SET}		2 8	mA	– Diagnosis output
4.1.12	N-1 current	I_{N-1}	-0.5	0.5	mA	_
4.1.13	Output current	I_{OUTx}	_	130	mA	_
Temper	atures					
4.1.14	Junction temperature	$T_{\rm j}$	-40	150	°C	_
4.1.15	Storage temperature	T_{stg}	-55	150	°C	_
ESD Su	sceptibility					
4.1.16	ESD resistivity to GND	V_{ESD}	-2	2	kV	Human Body Model (100 pF via $1.5 \text{ k}\Omega$) ²⁾
4.1.17	ESD resistivity all pins to GND	V_{ESD}	-500	500	V	CDM ³⁾
4.1.18	ESD resistivity corner pins to GND	V_{ESD}	-750	750	V	CDM ³⁾

¹⁾ Not subject to production test, specified by design

Note: Stresses above the ones listed here may cause permanent damage to the device. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

Note: Integrated protection functions are designed to prevent IC destruction under fault conditions described in the data sheet. Fault conditions are considered as "outside" normal operating range. Protection functions are not designed for continuous repetitive operation.

²⁾ ESD susceptibility, Human Body Model "HBM" according to ANSI/ESDA/JEDEC JS-001-2011

³⁾ ESD susceptibility, Charged Device Model "CDM" according to JESD22-C101E



General Product Characteristics

4.2 Functional Range

Pos.	Parameter	Symbol	Lim	Limit Values		Conditions	
			Min.	Max.			
4.2.19	Supply voltage range for normal operation	$V_{\mathrm{S(nom)}}$	5.5	40	V	-	
4.2.20	Power on reset threshold	$V_{\mathrm{S(POR)}}$	_	5	V	$\begin{split} V_{\text{EN}} &= V_{\text{S}} \\ R_{\text{SET}} &= 12 \text{ k}\Omega \\ I_{\text{OUTx}} &= 80\% \ I_{\text{OUTx(nom)}} \\ V_{\text{OUTx}} &= 2.5 \text{ V} \end{split}$	
4.2.21	Junction temperature	T_{j}	-40	150	°C	_	

Note: Within the functional range the IC operates as described in the circuit description. The electrical characteristics are specified within the conditions given in the related electrical characteristics table.

4.3 Thermal Resistance

Pos.	Parameter	Symbol		Limit Val	ues	Unit	Conditions
			Min.	Тур.	Max.		
4.3.1	Junction to Case	R_{thJC}	_	8	10	K/W	1) 2)
4.3.2	Junction to Ambient 1s0p board	R_{thJA1}				K/W	1) 3)
			_	61	_		$T_{\rm a}$ = 85 °C
			_	56	-		$T_{\rm a}$ = 85 °C $T_{\rm a}$ = 135 °C
4.3.3	Junction to Ambient 2s2p board	R_{thJA2}				K/W	1) 4)
			_	45	_		$T_{\rm a}$ = 85 °C
			_	43	_		$T_{\rm a}$ = 135 °C

- 1) Not subject to production test, specified by design. Based on simulation results.
- 2) Specified $R_{\rm thJC}$ value is simulated at natural convection on a cold plate setup (all pins and the exposed Pad are fixed to ambient temperature). $T_{\rm a}$ = 85°C, Total power dissipation 1.5 W.
- 3) The $R_{\rm thJA}$ values are according to Jedec JESD51-3 at natural convection on 1s0p FR4 board. The product (chip + package) was simulated on a 76.2 x 114.3 x 1.5 mm³ board with 70µm Cu, 300 mm² cooling area. Total power dissipation 1.5 W distributed statically and homogenously over all power stages.
- 4) The R_{thJA} values are according to Jedec JESD51-5,-7 at natural convection on 2s2p FR4 board. The product (chip + package) was simulated on a 76.2 x 114.3 x 1.5 mm³ board with 2 inner copper layers (outside 2 x 70 μ m Cu, inner 2 x 35 μ m Cu). Where applicable, a thermal via array under the exposed pad contacted the first inner copper layer. Total power dissipation 1.5 W distributed statically and homogenously over all power stages.



EN Pin

5 EN Pin

The EN pin is a dual function pin:

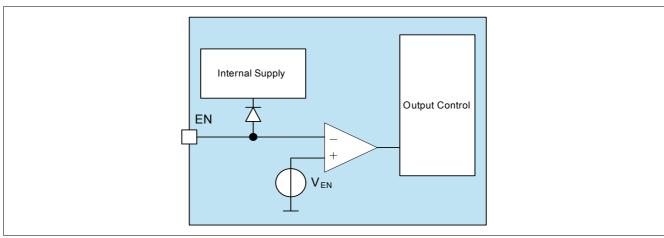


Figure 3 Block Diagram EN pin

Note: The current consumption at the EN-pin $I_{\rm EN}$ needs to be added to the total device current consumption. The total current consumption is the sum of the currents at the VS-pin $I_{\rm S}$ and the EN-pin $I_{\rm EN}$.

5.1 EN Function

If the voltage at the pin EN is below a threshold of $V_{\rm EN(off)}$ the LITIXTM Basic IC will enter Sleep mode. In this state all internal functions are switched off, the current consumption is reduced to $I_{\rm S(sleep)}$. A voltage above $V_{\rm EN(on)}$ at this pin enables the device after the Power on reset time $t_{\rm POR}$.

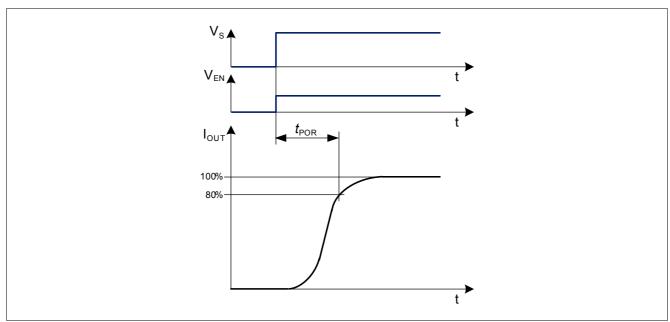


Figure 4 Power on reset



EN Pin

5.2 Internal Supply Pin

The EN pin can be used to supply the internal logic. There are two typical application conditions, where this feature can be used:

- 1) In "DC/DC control Buck" configurations, where the voltage $V_{\rm s}$ can be below 5.5V.
- 2) In configurations, where a PWM signal is applied at the Vbatt pin of a light module. The buffer capacitor $C_{\rm BUF}$ is used to supply the LITIXTM Basic IC during Vbatt low ($V_{\rm s}$ low) periods. This feature can be used to minimize the turn-on time to the values specified in **Pos. 10.2.15**. Otherwise, the power-on reset delay time $t_{\rm POR}$ (**Pos. 6.1.8**) has to be considered.

The capacitor can be calculated using the following formula:

$$C_{\text{BUF}} = t_{\text{LOW(max)}} \cdot \frac{I_{\text{EN(LS)}}}{V_{\text{S}} - V_{\text{D1}} - V_{\text{S(POR)}}} \tag{1}$$

See also a typical application drawing in Chapter 11.

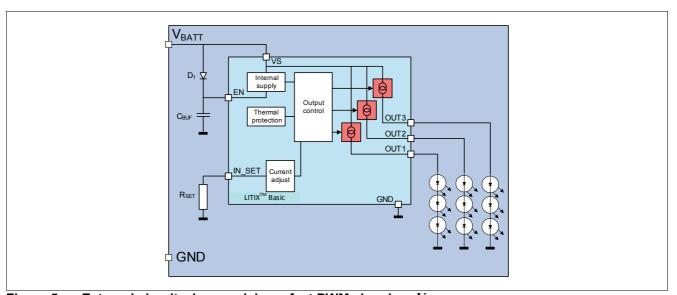


Figure 5 External circuit when applying a fast PWM signal on V_{BATT}



EN Pin

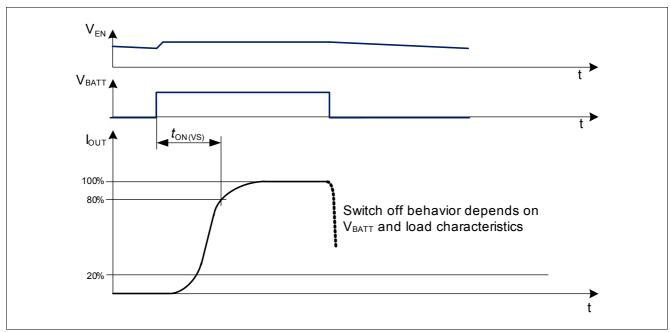


Figure 6 Typical waveforms when applying a fast PWM signal on V_{BATT}

The parameter $t_{\text{ON(VS)}}$ is defined at **Pos. 10.2.15**. The parameter $t_{\text{OFF(VS)}}$ depends on the load and supply voltage V_{BATT} characteristics.

5.3 EN Unused

In case of an unused EN pin, there are two different ways to connect it:

5.3.1 EN - Pull Up to VS

The EN pin can be connected with a pull up resistor (e.g. 10 k Ω) to V_s potential. In this configuration the LITIXTM Basic IC is always enabled.

5.3.2 EN - Direct Connection to VS

The EN pin can be connected directly to the VS pin (IC always enabled). This configuration has the advantage (compared to the configuration described in **Chapter 5.3.1**) that no additional external component is required.



6 DIS Pin

The DIS pin is designed as a single function pin.

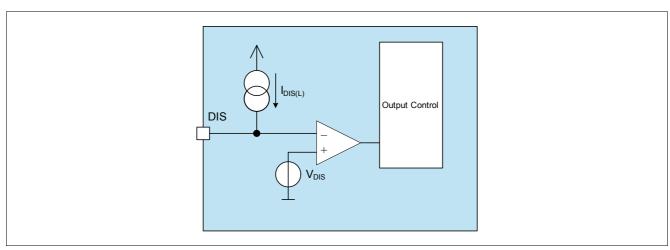


Figure 7 Block Diagram DIS pin

The pin can be used for PWM-dimming via a push-pull stage of a micro controller, which is connecting the DIS-pin to a low or high potential.

Note: The micro controller's push-pull stage has to be capable to sink currents according to **Pos. 6.1.17** to activate the device.

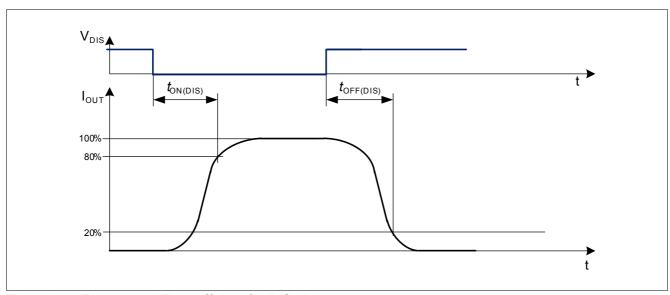


Figure 8 Turn on and Turn off time for DIS pin usage



6.1 Electrical Characteristics Internal Supply / EN / DIS Pin

Electrical Characteristics Internal Supply / EN / DIS pin

Unless otherwise specified: $V_{\rm S}$ = 5.5 V to 40 V, $T_{\rm j}$ = -40 °C to +150 °C, $R_{\rm SET}$ = 12 k Ω all voltages with respect to ground, positive current flowing into pin for input pins (I), positive currents flowing out of the I/O and output pins (O) (unless otherwise specified)

Pos.	Parameter	Symbol	Limit Values			Unit	Conditions
			Min.	Тур.	Max.		
6.1.1	Current consumption,	$I_{S(sleep)}$	_	0.1	2	μA	$^{1)}$ $V_{\rm EN}$ = 0.5 V
	sleep mode						<i>T</i> _i < 85 °C
							$\dot{V_{\rm S}}$ = 18 V
							V_{OUTx} = 3.6 V
6.1.2	Current consumption,	$I_{S(on)}$				mA	$^{2)}I_{IN_SET}=0\;\mu A$
	active mode						<i>T</i> _j < 105 °C
							$V_{\rm S}$ = 18 V
							V_{OUTx} = 3.6V
			_	_	1.4		$V_{\rm EN}$ = 5.5 V
			-	_	0.75		$V_{\rm EN}$ = 18 V
			-	_	1.5		$^{1)}R_{\rm EN}$ = 10 k Ω between
							VS and EN-pin
6.1.3	Current consumption,	$I_{\mathrm{S(dis,ST)}}$				mA	$^{2)} V_{\rm S}$ = 18 V
	device disabled via ST						$T_{\rm j}$ < 105 °C
							$V_{ST} = 5 \text{ V}$
			-	_	1.4		$V_{\rm EN}$ = 5.5 V
			-	_	0.65		$V_{\rm EN}$ = 18 V
			-	_	1.4		$^{1)}R_{EN}$ = 10 kΩ between
		_					VS and EN-pin
6.1.4	Current consumption,	$I_{\mathrm{S(dis,IN_SET)}}$				mA	$^{2)}V_{\rm S} = 18 \text{ V}$
	device disabled via IN_SET						$T_{\rm j}$ < 105 °C
							$V_{\text{IN_SET}} = 5 \text{ V}$
			-	_	1.4		$V_{\rm EN} = 5.5 \rm V$
			_	_	0.7		$V_{\rm EN}$ = 18 V
			_	_	1.4		¹⁾ R_{EN} = 10 kΩ between
		-					VS and EN-pin
6.1.5	Current consumption,	$I_{\mathrm{S(dis,DIS)}}$				mA	$^{2)}V_{\rm S} = 18 \text{ V}$
	device disabled via DIS						$T_{\rm j}$ < 105 °C
					4.0		$V_{\rm DIS} = 3.4 \text{ V}$
			-	-	1.6		$V_{\rm EN} = 5.5 \rm V$
			-	-	0.75		$V_{\rm EN}$ = 18 V
			-	_	1.6		$^{1)}$ R_{EN} = 10 kΩ between
							VS and EN-pin



Electrical Characteristics Internal Supply / EN / DIS pin (cont'd)

Unless otherwise specified: $V_{\rm S}$ = 5.5 V to 40 V, $T_{\rm j}$ = -40 °C to +150 °C, $R_{\rm SET}$ = 12 k Ω all voltages with respect to ground, positive current flowing into pin for input pins (I), positive currents flowing out of the I/O and output pins (O) (unless otherwise specified)

Pos.	Parameter	Symbol	Limit Values			Unit	Conditions
			Min.	Тур.	Max.		
6.1.6	Current consumption,	$I_{\mathrm{S(fault,STu)}}$				mA	$^{2)} V_{\rm S}$ = 18 V
	active mode in single fault						$T_{\rm j}$ < 105 °C
	detection condition with ST-						$R_{\text{SET}} = 12 \text{ k}\Omega$
	pin unconnected						$V_{\rm DIS} = 0.5 \text{V}$
					4 7		$V_{\text{OUTx}} = 18 \text{ V}$
			_	_	1.7 1.1		$V_{\rm EN} = 5.5 \rm V$
			_	_	1.8		$V_{\rm EN} = 18 \text{ V}$
			_	_	1.0		$^{1)}R_{EN}$ = 10 kΩ between VS and EN-pin
6.1.7	Current consumption,	$I_{\mathrm{S(fault,STG)}}$				mA	$^{2)} V_{\rm S} = 18 \text{ V}$
	active mode in single fault						$T_{\rm j}$ < 105 °C
	detection condition with ST-						$R_{\text{SET}} = 12 \text{ k}\Omega$
	pin connected to GND						$V_{\rm DIS} = 0.5 \rm V$
							$V_{\text{OUTx}} = 18 \text{ V}$
					6.0		$V_{\text{ST}} = 0 \text{ V}$
					4.9		$V_{\rm EN}$ = 5.5 V $V_{\rm EN}$ = 18 V
				_	5.9		$^{1)}R_{\text{EN}}$ = 10 kΩ between
					0.0		VS and EN-pin
6.1.8	Power-on reset delay time 3)	t_{POR}	_	_	25	μs	¹⁾ $V_{\rm S} = V_{\rm EN} = 0 \rightarrow 13.5 {\rm V}$
							$V_{OUTx(nom)}$ = 3.6 ± 0.3V
							I_{OUTx} = 80% $I_{\text{OUTx(nom)}}$
6.1.9	Required supply voltage for	$V_{S(on)}$	_	-	4	V	$V_{\rm EN} = 5.5 \rm V$
	output activation						$V_{\text{OUTx}} = 3 \text{ V}$
							$I_{\text{OUTx}} = 50\% I_{\text{OUTx(nom)}}$
6.1.10	Required supply voltage for	$V_{S(CC)}$	-	_	5.2	V	$V_{\rm EN} = 5.5 \rm V$
	current control						$V_{\rm OUTx} = 3.6 \text{ V}$
0.4.44	EN () I I	17			0.5	.,	$I_{\text{OUTx}} \ge 90\% I_{\text{OUTx(nom)}}$
6.1.11	EN turn on threshold	$V_{EN(on)}$	-	_	2.5	V	_
6.1.12	EN turn off threshold	$V_{EN(off)}$	0.8	_	-	V	4) 77
6.1.13	EN input current during low	$I_{EN(LS)}$	_	-	1.8	mA	$^{1)} V_{\rm S} = 4.5 \text{ V}$
	supply voltage						$T_{\rm j}$ < 105 °C
	ENILL COLUMN	7					V _{EN} = 5.5 V
6.1.14	EN high input current	$I_{EN(H)}$			0.4	mA	$T_{\rm j}$ < 105 °C
			-	_	0.1 0.1		$V_{\rm S}$ = 13.5 V, $V_{\rm EN}$ = 5.5 V
					1.65		$V_{\rm S}$ = 18 V, $V_{\rm EN}$ = 5.5 V $V_{\rm S}$ = $V_{\rm EN}$ = 18 V
				_	0.45		$V_{\rm S} - V_{\rm EN} - 10 \text{ V}$ $^{(1)}V_{\rm S} = 18 \text{ V}, R_{\rm EN} = 10 \text{ k}\Omega$
					0.43		between VS and EN-pin
6.1.15	DIS (active low)	$V_{DIS(L)}$	1.5	_	_	V	¹⁾ V _S = 818 V
	Switching low threshold						
	(outputs on)						



Electrical Characteristics Internal Supply / EN / DIS pin (cont'd)

Unless otherwise specified: $V_{\rm S}$ = 5.5 V to 40 V, $T_{\rm j}$ = -40 °C to +150 °C, $R_{\rm SET}$ = 12 k Ω all voltages with respect to ground, positive current flowing into pin for input pins (I), positive currents flowing out of the I/O and output pins (O) (unless otherwise specified)

Pos.	Parameter	Symbol	I	Limit Value	s	Unit	Conditions
			Min.	Тур.	Max.		
6.1.16	DIS (active low) Switching high threshold (outputs off)	V _{DIS(H)}	_	_	3.2	V	¹⁾⁴⁾ V _S = 818 V
6.1.17	DIS(active low) Low input current with active channels (voltage $< V_{\rm DIS(L)}$)	$I_{DIS(on)}$	I _{IN_SET} *3.1	I _{IN_SET} *4	I _{IN_SET} *4.9	μА	$^{1)}$ $T_{\rm j}$ = 25115 °C $I_{\rm IN_SET}$ = 100 μ A $V_{\rm DIS}$ = 1.7 $\rm V$ $V_{\rm EN}$ = 5.5 $\rm V$ $V_{\rm S}$ = 818 $\rm V$
6.1.18	DIS (active low) High input current	$I_{DIS(off)}$	-5	_	5	μΑ	$V_{\rm DIS} = 5 \text{ V}$ $V_{\rm EN} = 5.5 \text{ V}$ $V_{\rm S} = 818 \text{ V}$

¹⁾ Not subject to production test, specified by design

²⁾ The total device current consumption is the sum of the currents $I_{\rm S}$ and $I_{\rm EN(H)}$, please refer to Pos. 6.1.14

³⁾ See also Figure 4

⁴⁾ If TTL level compatibility is required, use μC open drain output with pull up resistor



IN_SET Pin

7 IN_SET Pin

The IN_SET pin is a multiple function pin for output current definition, input and diagnostics:

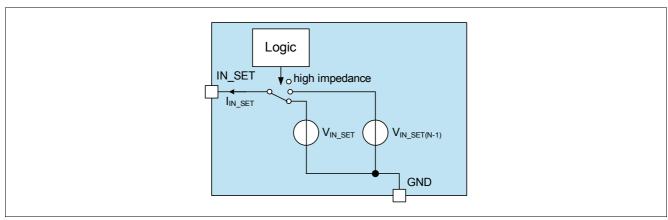


Figure 9 Block Diagram IN_SET pin

7.1 Output Current Adjustment via RSET

The output current for all three channels can only be adjusted simultaneously. The current adjustment can be done by placing a low power resistor (R_{SET}) at the IN_SET pin to ground. The dimensioning of the resistor can be done using the formula below:

$$R_{\text{SET}} = \frac{k}{I_{\text{OUT}}} \tag{2}$$

The gain factor k ($R_{\rm SET}$ * output current) is specified in **Pos. 10.2.4** and **Pos. 10.2.5**. The current through the $R_{\rm SET}$ is defined by the resistor itself and the reference voltage $V_{\rm IN_SET(ref)}$, which is applied to the IN_SET during supplied device.

7.2 Smart Input Pin

The IN_SET pin can be connected via $R_{\rm SET}$ to the open-drain output of a $\mu \rm C$ or to an external NMOS transistor as described in Figure 10. This signal can be used to turn off the output stages of the IC. A minimum IN_SET current of $I_{\rm IN_SET(act)}$ is required to turn on the output stages. This feature is implemented to prevent glimming of LEDs caused by leakage currents on the IN_SET pin, see Figure 13 for details. In addition, the IN_SET pin offers the diagnostic feedback information, if the status pin is connected to GND. Another diagnostic possibility is shown in Figure 11, where the diagnosis information is provided via the ST pin (refer to Chapter 8 and Chapter 9) to a micro controller. In case of a fault event with the ST pin connected to GND the IN_SET voltage is increased to $V_{\rm IN_SET(N-1)}$ Pos. 9.3.2. Therefore, the device has two voltage domains at the IN_SET-pin, which is shown in Figure 14.



IN_SET Pin

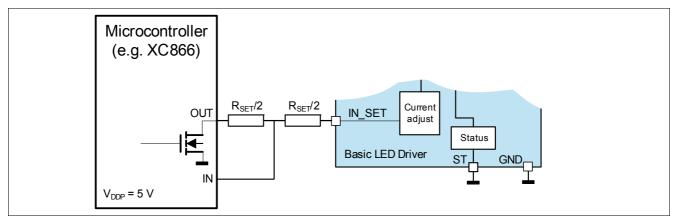


Figure 10 Schematics IN_SET interface to μC, diagnosis via IN_SET pin

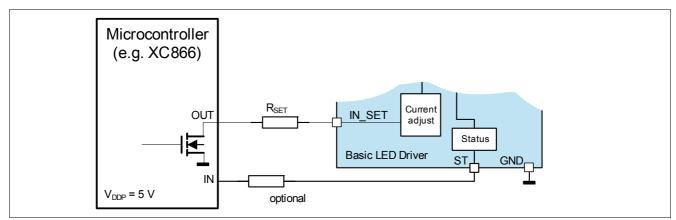


Figure 11 Schematics IN_SET interface to μC, diagnosis via ST pin

The resulting switching times are shown in Figure 12:

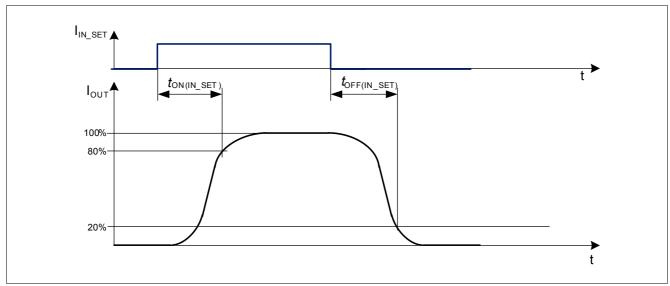


Figure 12 Switching times via IN_SET



IN_SET Pin

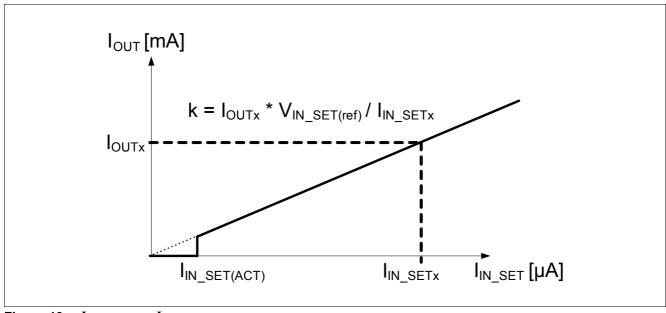


Figure 13 $I_{
m OUT}$ versus $I_{
m INSET}$

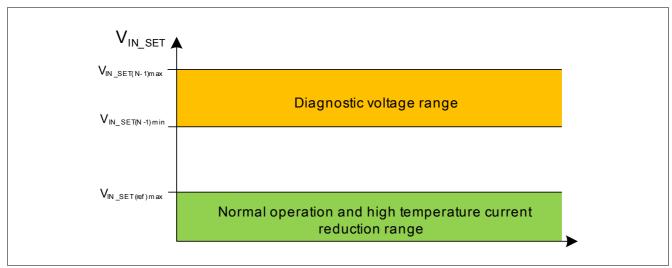


Figure 14 Voltage domains for IN_SET pin, if ST pin is connected to GND



ST Pin

8 ST Pin

The ST pin is a multiple function pin.

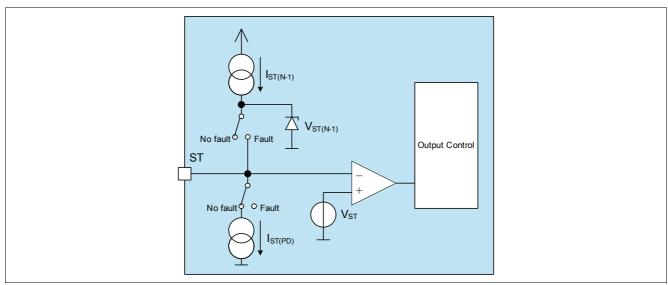


Figure 15 Block Diagram ST pin

8.1 Diagnosis Selector

If the status pin is unconnected or connected to GND via a high ohmic resistor ($V_{\rm ST}$ to be below $V_{\rm ST(L)}$), the ST pin acts as diagnosis output pin. In normal operation (device is activated) the ST pin is pulled to GND via the internal pull down current $I_{\rm ST(PD)}$. In case of an open load condition the ST pin is switched to $V_{\rm ST(N-1)}$ after the N-1 detection filter time.

If the device is operated in PWM operation via the VS and/or EN pins the ST pin should be connected to GND via a high ohmic resistor (e.g. $470k\Omega$) to ensure proper device behavior during fast rising VS and/or EN slopes.

If the ST pin is shorted to GND the diagnostic feedback is performed via the IN_SET-pin, which is shown in **Chapter 7.2** and **Chapter 9**.

8.2 Diagnosis Output

If the status pin is unconnected or connected to GND via a high ohmic resistor ($V_{\rm ST}$ to be below $V_{\rm ST(L)}$), it acts as a diagnostic output. In case of a fault condition the ST pin rises its voltage to $V_{\rm ST(N-1)}$ (Pos. 9.3.7). Details are shown in Chapter 9.

8.3 Disable Input

If an external voltage higher than $V_{\rm ST(H)}$ (Pos. 9.3.5) is applied to the ST pin, the device is switched off. This function is used for applications, where multiple drivers should be used for one light function. It is possible to combine the drivers' fault diagnosis via the ST pins. If a single LED chain fails, the entire light function is switched off. In this scenario e.g. the diagnostic circuit on the body control module can easily distinguish between the two cases (normal load or load fault), because nearly no current is flowing into the LED module during the fault scenario - the drivers consume a current of $I_{\rm S(fault,STu)}$ (Pos. 6.1.6) or $I_{\rm S(dis,ST)}$ (Pos. 6.1.3).

As soon as one LED chain fails, the ST-pin of this device is switched to $V_{\rm ST(N-1)}$. The other devices used for the same light function can be connected together via the ST pins. This leads to a switch off of all devices connected together. Application examples are shown in **Chapter 11**.



ST Pin

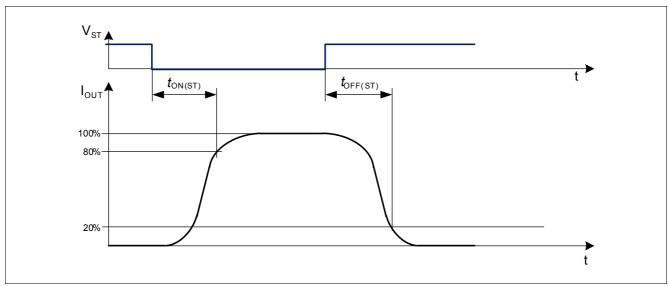


Figure 16 Switching times via ST Pin



9 Load Diagnosis

9.1 N-1 Detection

The N-1 diagnosis is specially designed to detect error conditions in LED arrays with multiple LED chains used for one light function. If one LED within one chain fails in open condition the respective LED chain is off. Different automotive applications require a complete deactivation of a light function, if the desired brightness of the function (LED array) can not be achieved due to an internal error condition. Such a deactivation feature is integrated in the LITIXTM Basic IC.

The functionality of the N-1 pin is shown in the following block diagram:

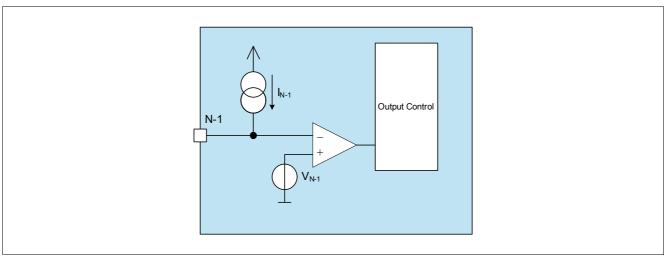


Figure 17 Block Diagram N-1 pin

In applications, where more than one LITIXTM Basic IC is used, the devices can be connected via the ST pins as shown in **Figure 21**. This circuit can be used to disable all output stages (of all LITIXTM Basic ICs) during an open load event on one channel. The outputs are deactivated after a N-1 filter time t_{N-1} , which is defined by the charging current I_{N-1} (**Pos. 9.3.10**). The time is adjustable with a capacitor connected to the N-1 pin according the following equation:

$$t_{\rm typ} = \frac{C_{\rm N-1} \cdot V_{\rm N-1(th)}}{I_{\rm N-1}} \tag{3}$$



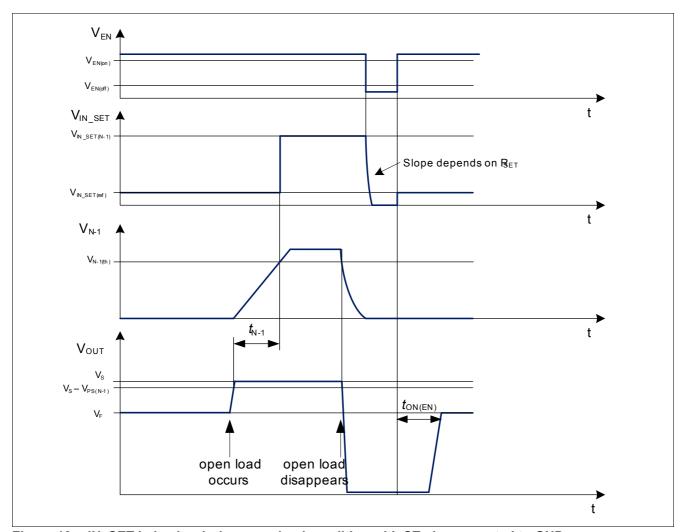


Figure 18 IN_SET behavior during open load condition with ST pin connected to GND



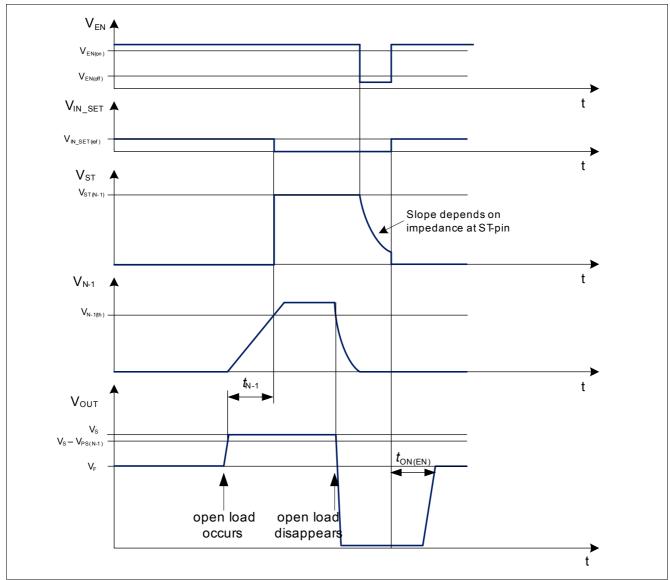


Figure 19 IN_SET and ST behavior during open load condition (ST unconnected)

The N-1 status is latched. The output stages can be re-enabled by a Low to High transition at the EN pin or by a Power on reset. To provide a Limp Home functionality (lower number of LEDs instead of complete deactivation) in the case of a partially damaged LED array, the N-1 filter time $t_{\rm N-1}$ can be used. If a PWM signal with an ON-time of less than $t_{\rm N-1}$ is applied to the VS and EN pins, the N-1 detection feature will not be activated.

If there is more than one device used for N-1 detection the maximum number of devices, which can be connected as shown in **Figure 21**, is limited to n_{N-1} . The maximum number of devices in N-1 configuration is calculated



according to **Equation (4)**, and the precondition of **Equation (5)** has to be fulfilled. The pull-down resistor R_{DIS} is calculated according to **Equation (6)** and **Equation (7)**.

$$n_{N-1} \le \frac{\left(I_{\text{IN_SET(OL,min)}} - \frac{V_{\text{DIS(H, max)}} + V_{\text{F}}}{R_{\text{SET(min)}}}\right) \cdot V_{\text{DIS(H, min)}} \cdot R_{\text{SET(min)}}}{V_{\text{DIS(H, max)}} \cdot 4 \cdot V_{\text{IN SET(max)}}}$$
(4)

$$\frac{V_{\text{DIS}(\text{H, min})} \cdot V_{\text{IN_SET(min)}} \cdot R_{\text{SET(min)}}}{(V_{\text{IN_SET(max)}})^2 \cdot R_{\text{SET(max)}}} > 1$$
(5)

$$R_{\text{DIS(min)}} = \frac{V_{\text{DIS(H, max)}}}{I_{\text{IN_SET(OL,min)}} - \frac{V_{\text{DIS(H, max)}} + V_{\text{F}}}{R_{\text{SET(max)}}}}$$
(6)

$$R_{\rm DIS(max)} = \frac{V_{\rm DIS(H, min)}}{n_{\rm N-1} \cdot 4 \cdot \frac{V_{\rm IN \ SET(max)}}{R_{\rm SET(min)}}}$$
(7)

 $V_{\rm F}$ represents the voltage drop across the diode between the IN_SET- and the DIS-pin.

Note: If one channel of the device should not be used, the according output needs to be connected to GND, which leads to a disabling of this output.

Note: In case of a double fault, where the loads of two channels are faulty at the same time, the device operates as in normal operation. This feature is implemented to avoid any unwanted switch off during significant supply voltage drops. Please refer to **Chapter 9.2**.

9.2 Double Fault Conditions

The TLD1311EL has an integrated double fault detection feature. This feature is implemented to detect significant supply voltage drops. During such supply voltage drops close to the forward voltage of the LEDs the drivers outputs remain active. In case of load faults on two or more outputs within the time period t_{N-1} the device disables the diagnosis to avoid any uncorrect open load diagnosis during low supply voltages close to the forward voltages of the connected LED chains. If the faults between two or three channels happen with a delay of longer than t_{OL} the double fault detection feature is not active, i.e. the device is not turned on.

9.3 Electrical Characteristics IN_SET Pin and Load Diagnosis

Electrical Characteristics IN_SET pin and Load Diagnosis

Unless otherwise specified: $V_{\rm S}$ = 5.5 V to 40 V, $T_{\rm j}$ = -40 °C to +150 °C, $R_{\rm SET}$ = 12 k Ω , all voltages with respect to ground, positive current flowing into pin for input pins (I), positive currents flowing out of the I/O and output pins (O) (unless otherwise specified)

Pos.	Parameter	er Symbol Limit Valu		lues Unit		Conditions	
			Min.	Тур.	Max.		
9.3.1	IN_SET reference voltage	V _{IN_SET(ref)}	1.19	1.23	1.27	V	$V_{\text{OUTx}} = 3.6 \text{ V}$ $T_{\text{j}} = 25115 \text{ °C}$
9.3.2	IN_SET N_1 voltage	V _{IN_SET(N-1)}	4	_	5.5	V	$T_{\rm S} > 8 \text{ V}$ $T_{\rm j} = 25150 \text{ °C}$ $V_{\rm S} = V_{\rm OUTx} \text{ (OL)}_{\rm x}$